

ZXTP23015CFH 15V, SOT23, PNP medium power transistor

Summary

 $V_{(BR)CES} > -15V, V_{(BR)CEO} > -15V$

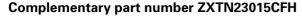
 $V_{(BR)ECO} > -6V$

 $I_{C(CONT)} = -6A$

 $R_{CE(SAT)} = 20m\Omega \text{ typical}$

 $V_{CE(SAT)} < -36mV @ -1A$

 $P_D = 1.25W$



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

Feature

- Higher power dissipation SOT23 package
- · High peak current
- · Low saturation voltage
- · 15V forward blocking voltage
- · 6V reverse blocking voltage

Applications

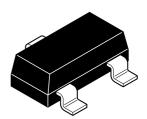
- · High side disconnect switches
- · DC DC converters
- MOSFET and IGBT gate driving
- Motor drive
- · Relay, lamp, and solenoid drive

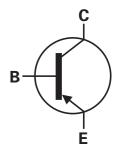
Ordering information

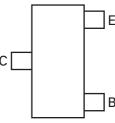
| Device | Reel size (inches) | Tape width | Quantity per reel |
|----------------|-----------------------|------------|-------------------|
| ZXTP23015CFHTA | 7 | 8mm | 3000 |

Device marking

317







Pinout - top view

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|-----------------------------------------------------------------------------------------------|----------------------------------|----------------|------------|
| Collector-base voltage | V _{CBO} | -15 | V |
| Collector-emitter voltage | V _{(BR)CES} | -15 | V |
| Collector-emitter voltage | V _{CEO} | -15 | V |
| Emitter-base voltage | V _{EBO} | -7.0 | V |
| Emitter-collector voltage | V _{ECO} | -6.0 | V |
| Peak pulse current | I _{CM} | -10 | А |
| Continuous collector current (c) | Ic | -5 | А |
| Continuous collector current (d) | Ic | -6 | Α |
| Base current | I _B | -1.2 | А |
| Power dissipation @ T _A =25°C ^(a) Linear derating factor ^(a) | P _D | 0.73 5.84 | W mW/°C |
| Power dissipation @ T _A =25°C ^(b) Linear derating factor ^(b) | P _D | 1.05 8.4 | W mW/°C |
| Power dissipation @ T _A =25°C ^(c) Linear derating factor ^(c) | P _D | 1.25 9.6 | W mW/°C |
| Power dissipation @ T _A =25°C ^(d) Linear derating factor ^(d) | P _D | 1.81 14.5 | W mW/°C |
| Operating and storage temperature | T _j :T _{stg} | -55 to +150 | °C |

Thermal resistance

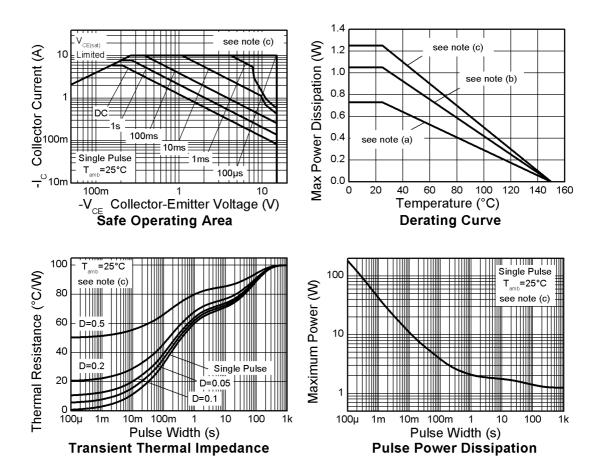
| Parameter | Symbol | Value | Unit |
|------------------------------------|----------------|-------|------|
| Junction to ambient ^(a) | $R\Theta_{JA}$ | 171 | °C/W |
| Junction to ambient ^(b) | $R\Theta_{JA}$ | 119 | °C/W |
| Junction to ambient ^(c) | $R\Theta_{JA}$ | 100 | °C/W |
| Junction to ambient ^(d) | $R\Theta_{JA}$ | 69 | °C/W |

NOTES:

⁽a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

⁽b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (d) As (c) above measured at t<5secs.

Characteristics



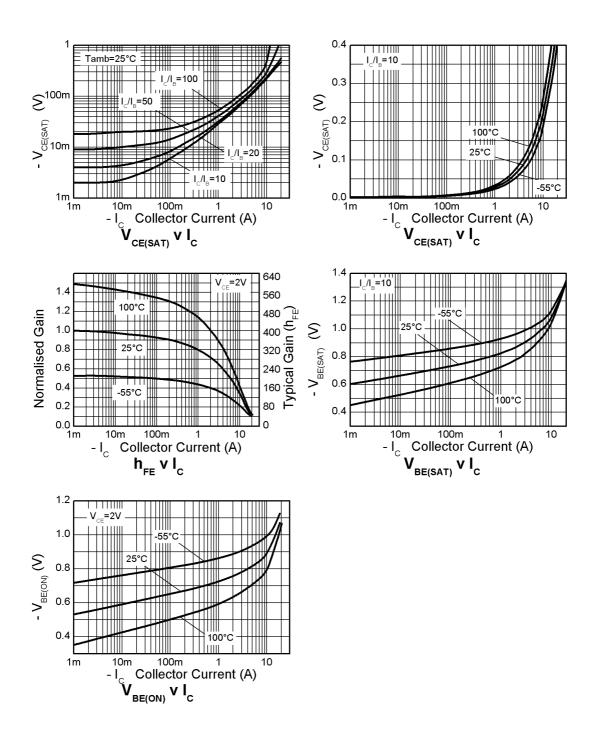
ELECTRICAL CHARACTERISTICS (at $T_{AMB} = 25$ °C unless otherwise stated)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---------------------------------------|----------------------|------|-------|-------|------|--------------------------------------------------------------|
| Collector-base breakdown voltage | V _{(BR)CBO} | -15 | -40 | | V | I _C =-100μA |
| Collector-emitter breakdown voltage | V _{(BR)CES} | -15 | -40 | | V | I _C =-100μA |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | -15 | -25 | | V | I _C =-10mA ^(*) |
| Emitter-base breakdown voltage | V _{(BR)EBO} | -7.0 | -8.2 | | V | I _E =-100μA |
| Emitter-collector breakdown voltage | V _{(BR)ECO} | -6.0 | -8.5 | | V | l _E =-100μA |
| Collector-emitter cut-off current | I _{CES} | | | -20 | nA | V _{CE} =-12V |
| Collector-base cut-off current | I _{CBO} | | | -20 | nA | V _{CB} =-12V |
| Emitter-base cut-off current | I _{EBO} | | | -10 | nA | V _{EB} =-6V |
| Static forward current transfer ratio | H _{FE} | 200 | 380 | | | I _C =-10mA, V _{CE} =-2V ^(*) |
| ratio | | 200 | 350 | 560 | | I _C =-500mA, V _{CE} =-2V |
| | | 140 | 220 | | | Ic=-6A, V _{CE} =-2V |
| Collector-emitter saturation | V _{CE(sat)} | | -6 | -10 | mV | I _C =-100mA, I _B =-10mA ^(*) |
| voltage | | | -27 | -36 | mV | I _C =-1A, I _B =-100mA ^(*) |
| | | | -90 | -120 | mV | I _C =-3A, I _B =-60mA ^(*) |
| | | | -140 | -190 | mV | I _C =-6A, I _B =-240mA ^(*) |
| Base-emitter saturation voltage | V _{BE(sat)} | | -0.83 | -0.93 | V | I _C =-3A, I _B =-60mA ^(*) |
| | | | -0.93 | -1.03 | V | I _C =-6A, I _B =-240mA ^(*) |
| Base-emitter turn-on voltage | V _{BE(on)} | | -0.83 | -0.93 | V | I _C =-6A, V _{CE} =-2V ^(*) |
| Transition frequency | f _T | | 270 | | MHz | Ic=-500mA, V _{CE} =-2V, f=50MHz |
| Output capacitance | C _{obo} | | 78.4 | | pF | V _{CB} =-10V, f=1MHz |
| Delay time | t (d) | | 16 | | ns | V _{CC} =-5V, I _C =-3A, |
| Rise time | t (r) | | 13 | | ns | I _{B1} =I _{B2} =-150mA |
| Storage time | t _(stg) | | 123 | | ns | |
| Fall time | t _(f) | | 9 | | ns | |

NOTES:

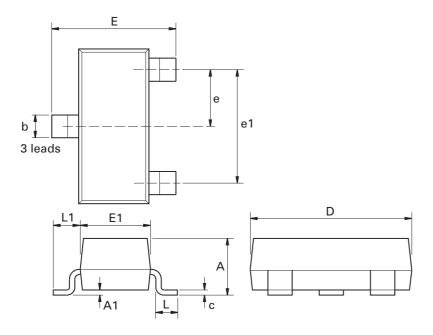
(*) Measured under pulsed conditions. Pulse width = 300 μS . Duty cycle ${\le}2\%$.

Typical characteristics



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Package outline - SOT23



| Dim. | Millin | neters | Inc | hes | Dim. | Millimeters | | Inches | |
|------|--------|--------|--------|-------|------|-------------|------|-----------|--------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| Α | - | 1.12 | - | 0.044 | e1 | 1.90 NOM | | 0.075 NOM | |
| A1 | 0.01 | 0.10 | 0.0004 | 0.004 | Е | 2.10 | 2.64 | 0.083 | 0.104 |
| b | 0.30 | 0.50 | 0.012 | 0.020 | E1 | 1.20 | 1.40 | 0.047 | 0.055 |
| С | 0.085 | 0.20 | 0.003 | 0.008 | L | 0.25 | 0.60 | 0.0098 | 0.0236 |
| D | 2.80 | 3.04 | 0.110 | 0.120 | L1 | 0.45 | 0.62 | 0.018 | 0.024 |
| е | 0.95 | NOM | 0.037 | NOM | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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